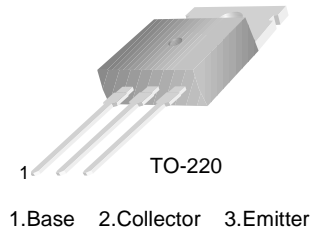


BDW94/A/B/C

Power Linear and Switching Applications

- Power Darlington TR
- Complement to BDW93, BDW93A, BDW93B and BDW93C respectively



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage		
	: BDW94	- 45	V
	: BDW94A	- 60	V
	: BDW94B	- 80	V
V_{CEO}	Collector-Base Voltage	- 100	V
	: BDW94	- 45	V
	: BDW94A	- 60	V
	: BDW94B	- 80	V
I_C	Collector-Base Voltage	- 100	V
	: BDW94	- 45	V
	: BDW94A	- 60	V
	: BDW94B	- 80	V
I_{CP}	Collector-Base Voltage	- 100	V
I_B	Collector-Base Voltage	- 100	V
P_C	Collector Current (DC)	- 12	A
T_J	*Collector Current (Pulse)	- 15	A
T_{STG}	Base Current	- 0.2	A
	Collector Dissipation ($T_C=25^\circ\text{C}$)	80	W
	Junction Temperature	150	$^\circ\text{C}$
	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage : BDW94 : BDW94A : BDW94B : BDW94C	$I_C = -100\text{mA}, I_B = 0$	- 45 - 60 - 80 - 100			V V V V
I_{CBO}	Collector Cut-off Current : BDW94 : BDW94A : BDW94B : BDW94C	$V_{CB} = -45\text{V}, I_E = 0$ $V_{CB} = -60\text{V}, I_E = 0$ $V_{CB} = -80\text{V}, I_E = 0$ $V_{CB} = -100\text{V}, I_E = 0$			- 100 - 100 - 100 - 100	μA μA μA μA
I_{CEO}	Collector Cut-off Current : BDW94 : BDW94A : BDW94B : BDW94C	$V_{CE} = -45\text{V}, I_B = 0$ $V_{CE} = -60\text{V}, I_B = 0$ $V_{CE} = -80\text{V}, I_B = 0$ $V_{CE} = -100\text{V}, I_B = 0$			- 1 - 1 - 1 - 1	mA mA mA mA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = -5\text{V}, I_C = 0$			- 2	mA
h_{FE}	* DC Current Gain	$V_{CE} = -3\text{V}, I_C = -3\text{A}$ $V_{CE} = -3\text{V}, I_C = -5\text{A}$ $V_{CE} = -3\text{V}, I_C = -10\text{A}$	1000 750 100		20000	
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = -5\text{A}, I_B = -20\text{mA}$ $I_C = -10\text{A}, I_B = -100\text{mA}$			- 2 - 3	V V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = -5\text{A}, I_B = -20\text{mA}$ $I_C = -10\text{A}, I_B = -100\text{mA}$			- 2.5 - 4	V V
V_F	* Parallel Diode Forward Voltage	$I_F = -5\text{A}$ $I_F = -1.0\text{A}$		- 1.3 - 1.8	- 2 - 4	V V

* Pulse Test: $PW=300\mu\text{s}$, duty Cycle = 1.5% Pulsed

Typical Characteristics

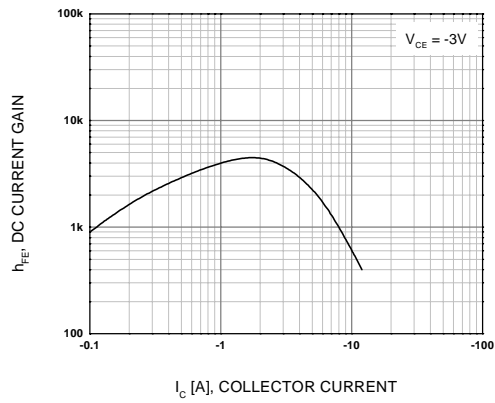


Figure 1. DC Current Gain

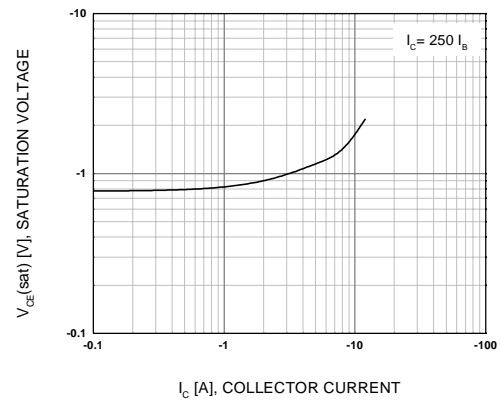


Figure 2. Collector-Emitter Saturation Voltage

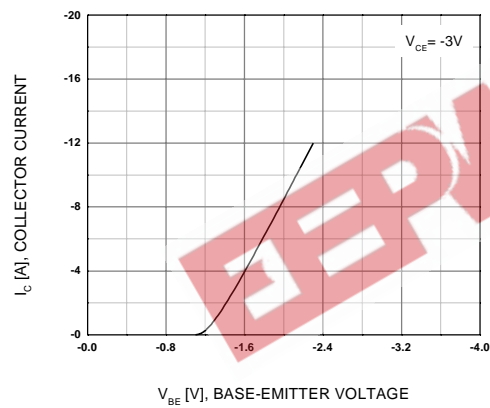


Figure 3. Base-Emitter On Voltage

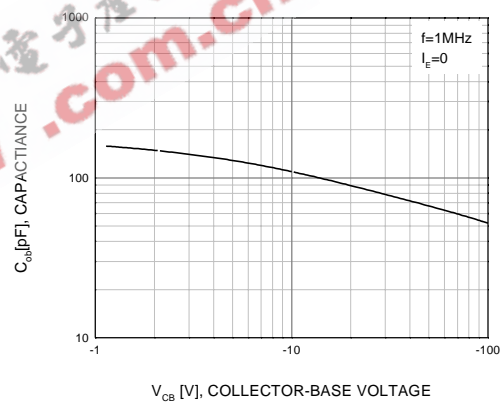


Figure 4. Output Capacitance

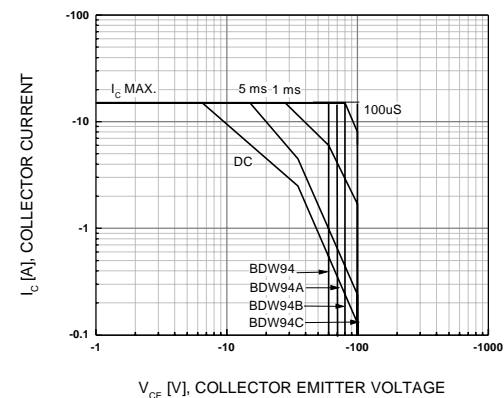


Figure 5. Safe Operating Area

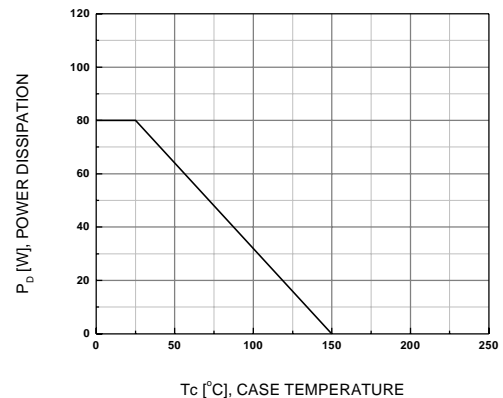
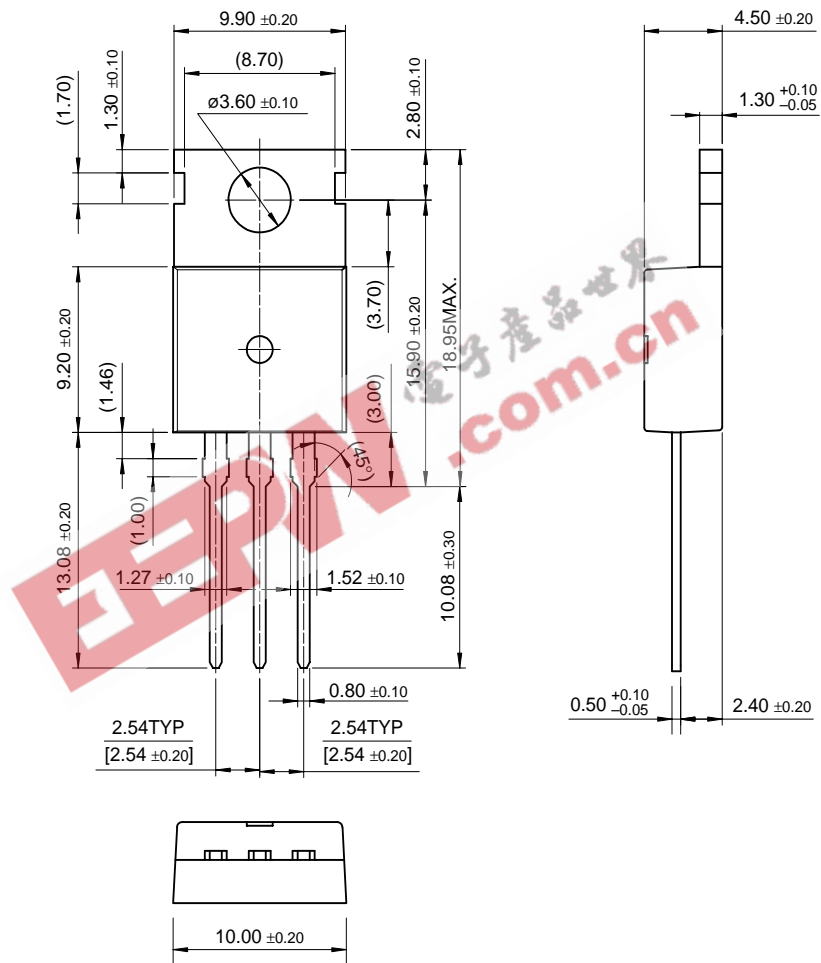


Figure 6. Power Derating

Package Dimensions

TO-220



Dimensions in Millimeters

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